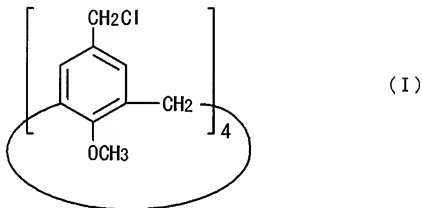


AMENDMENTS TO THE CLAIMS

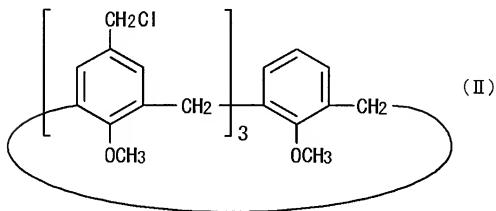
1. (Canceled)

2. (Original) A resist comprising at least one of 5,11,17,23 - tetrachloromethyl - 25,26,27,28 - tetramethoxycalix [4] arene (CMC4AOMe) represented by the structural formula (I) of the following chemical formula 3 and 5,11,17 - trichloromethyl - 25,26,27,28 - tetramethoxycalix [4] arene (CMC3AOMe) represented by the structural formula (II) of the following chemical formula 4.

[Chemical Formula 3]

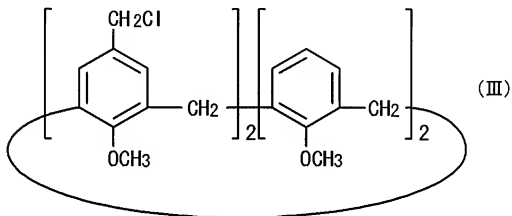


[Chemical Formula 4]

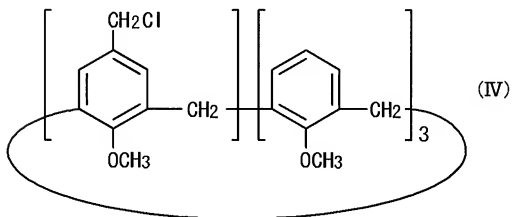


3. (Original) The resist according to claim 2, further comprising at least one of 5,11 – dichloromethyl – 25,26,27,28 – tetramethoxycalix [4] arene (CMC2AOMe) represented by the structural formula (III) of the following chemical formula 5 and 5 – monochloromethyl – 25,26,27,28 – tetramethoxycalix [4] arene (CMC1AOMe) represented by the structural formula (IV) of the following chemical formula 6 is provided.

[Chemical Formula 5]



[Chemical Formula 6]



4. (Previously Presented) The resist according to claim 2, further comprising at least one of oligomer and organic polymer compound.

5. (Previously Presented) The resist according to claim 2, which is exposed by the irradiation of at least one of electronic beam, X-ray, ion beam and atomic beam.

6. (Previously Presented) The resist according to claim 2, further comprising, at least one solvent selected from the group consisting of ethyl lactate (EL), propylene glycol monomethyl ether (PGME), propylene glycol monomethyl ether acetate (PGMEA), ethyl propionate, n-butyl acetate and 2-heptanone.

7. (Original) A method for forming a resist pattern comprising the following steps of coating the resist according to claim 6 on a substrate, exposing said resist to a radioactive ray; and a step developing said resist.

8. (Original) The method according to claim 7,

Wherein said radioactive ray is any of electronic beam, X-ray, ion beam and atomic beam.

9. (Previously Presented) The method according to claim 7,

wherein said developing step is carried out by using a developer comprising at least one selected from the group consisting of ethyl lactate (EL), propylene glycol monomethyl ether

(PGME), propylene glycol monomethyl ether acetate (PGMEA), ethyl propionate, n-butyl acetate, 2-heptanone and tetramethyl ammonium hydroxide.

10. (Previously Presented) A method for hyperfine processing comprising the steps of forming a resist pattern using the resist pattern forming method according to claim 7; and performing a processing on said substrate with said resist pattern as a mask.

11. (Previously Presented) The resist according to claim 3, further comprising at least one of oligomer and organic polymer compound.